Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

CGHV27200

200 W, 2500-2700 MHz, GaN HEMT for LTE

Cree's CGHV27200 is a gallium nitride (GaN) high electron mobility transistor (HEMT) is designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGHV27200 ideal for 2.5-2.7 GHz LTE and BWA amplifier applications. The transistor is input matched and supplied in a ceramic/metal flange package.

Package Type: 440162 and 440161
PN: CGHV27200F and CGHV27200P

Typical Performance Over 2.5 - 2.7 GHz (T_c = 25°C) of Demonstration Amplifier

Parameter	2.5 GHz	2.6 GHz	2.7 GHz	Units
Gain @ 46 dBm	15.0	16.0	16.0	dB
ACLR @ 46 dBm	-36.5	-37.5	-37.0	dBc
Drain Efficiency @ 46 dBm	29.0	28.5	29.0	%

Note:
Measured in the CGHV27200-AMP amplifier circuit, under WCDMA 3GPP test model 1, 64 DPCH, 45% clipping, PAR = 7.5 dB @ 0.01% Probability on CCDF.

Features

RoHS COMPLIANT

- 2.5 - 2.7 GHz Operation
- 16 dB Gain
- -37 dBc ACLR at 40 W P_{AVE}
- 29 % Efficiency at 40 W P_{AVE}
- High Degree of DPD Correction Can be Applied

Large Signal Models Available for ADS and MWO

Absolute Maximum Ratings (not simultaneous) at 25˚C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	125	Volts	25˚C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25˚C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	32	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	12	A	25˚C
Soldering Temperature[2]	T_S	245	˚C	
Screw Torque	τ	80	in-oz	
Thermal Resistance, Junction to Case[3]	$R_{\theta JC}$	1.22	˚C/W	85˚C, P_{DISS} = 96 W
Thermal Resistance, Junction to Case[4]	$R_{\theta JC}$	1.54	˚C/W	85˚C, P_{DISS} = 96 W
Case Operating Temperature[5]	T_C	-40, +150	˚C	

Note:
[1] Current limit for long term, reliable operation.
[2] Refer to the Application Note on soldering at http://www.cree.com/rf/document-library
[3] Measured for the CGHV27200P
[4] Measured for the CGHV27200F
[5] See also, the Power Dissipation De-rating Curve on Page 6

Electrical Characteristics (T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 32 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DS} = 50 V, I_D = 1.0 A
Saturated Drain Current[2]	I_{DS}	24	28.8	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	150	–	–	V_{DC}	V_{GS} = -8 V, I_D = 32 mA
RF Characteristics[5] (T_C = 25˚C, F_0 = 2.7 GHz unless otherwise noted)						
Saturated Output Power[3,4]	P_{SAT}	–	300	–	W	V_{DD} = 50 V, I_{DQ} = 1.0 A
Pulsed Drain Efficiency[3]	η	–	62	–	%	V_{DD} = 50 V, I_{DQ} = 1.0 A, P_{OUT} = P_{SAT}
Gain[6]	G	–	15.25	–	dB	V_{DD} = 50 V, I_{DQ} = 1.0 A, P_{OUT} = 46 dBm
WCDMA Linearity[6]	ACLR	–	-37	–	dBc	V_{DD} = 50 V, I_{DQ} = 1.0 A, P_{OUT} = 46 dBm
Drain Efficiency[6]	η	–	30.5	–	%	V_{DD} = 50 V, I_{DQ} = 1.0 A, P_{OUT} = 46 dBm
Output Mismatch Stress[3]	VSWR	–	–	10 : 1	Ψ	No damage at all phase angles, V_{DD} = 50 V, I_{DQ} = 1.0 A, P_{OUT} = 200 W Pulsed
Dynamic Characteristics						
Input Capacitance[7]	C_{GS}	–	97	–	pF	V_{DS} = 50 V, V_{gs} = -8 V, f = 1 MHz
Output Capacitance[7]	C_{DS}	–	13.4	–	pF	V_{DS} = 50 V, V_{gs} = -8 V, f = 1 MHz
Feedback Capacitance	C_{GD}	–	0.94	–	pF	V_{DS} = 50 V, V_{gs} = -8 V, f = 1 MHz

Notes:
[1] Measured on wafer prior to packaging.
[2] Scaled from PCM data.
[3] Pulse Width = 100 µS, Duty Cycle = 10%
[4] P_{SAT} is defined as I_G = 3 mA peak.
[5] Measured in CGHV27200-AMP.
[6] Single Carrier WCDMA, 3GPP Test Model 1, 64 DPCH, 45% Clipping, PAR = 7.5 dB @ 0.01% Probability on CCDF.
[7] Includes package and internal matching components.

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Typical Performance

Figure 1. - Small Signal Gain and Return Losses vs Frequency for the CGHV27200 measured in CGHV27200-AMP Amplifier Circuit
V_{DD} = 50 V, I_{DQ} = 1.0 A

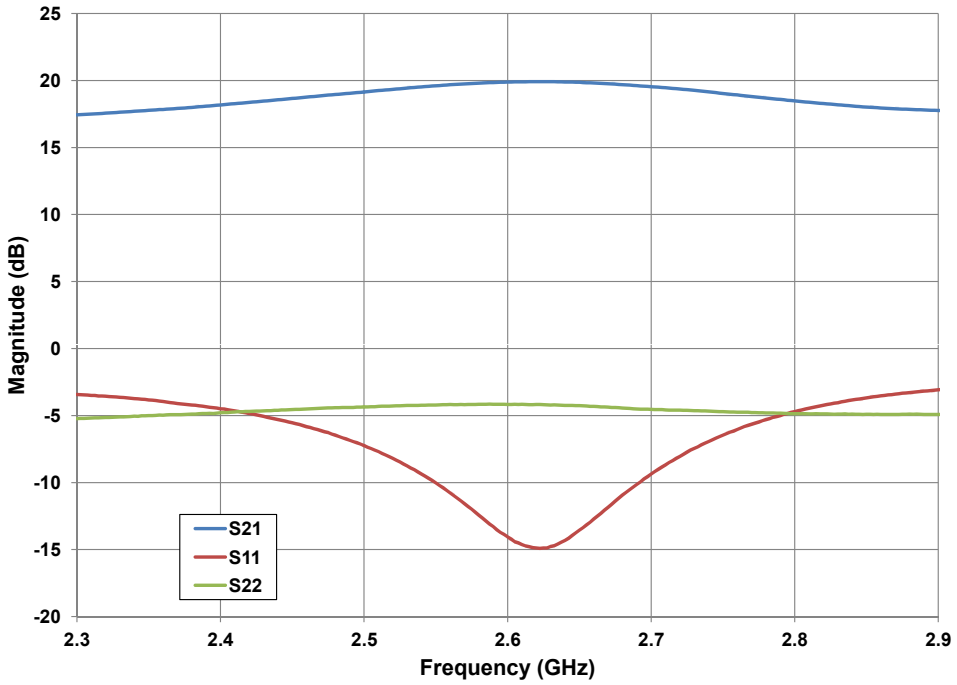
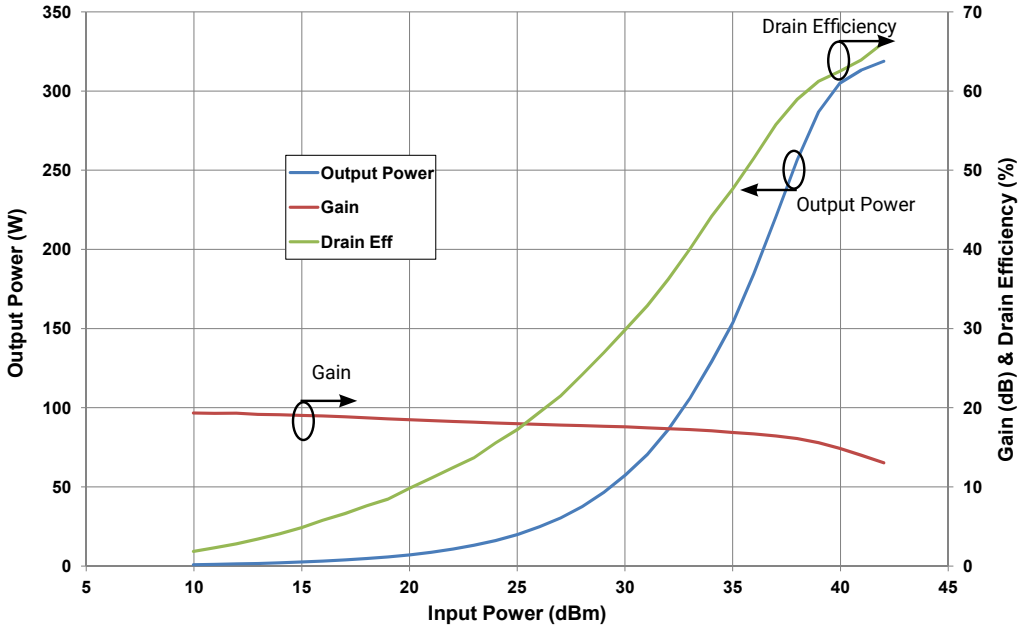


Figure 2. - Typical Pulsed Measurements vs Input Power of the CGHV27200 measured in CGHV27200-AMP Amplifier Circuit.
V_{DS} = 50 V, I_{DQ} = 1.0 A, Freq = 2.6 GHz, Pulse Width = 100 µs, Duty Cycle = 10 %



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Typical Performance

Figure 3. - Typical Linearity vs Output Power for the CGHV27200 measured in CGHV27200-AMP Amplifier Circuit V_{DD} = 50 V, I_{DQ} = 1.0 A, Freq = 2.6 GHz, 1c WCDMA 7.5 dB PAR

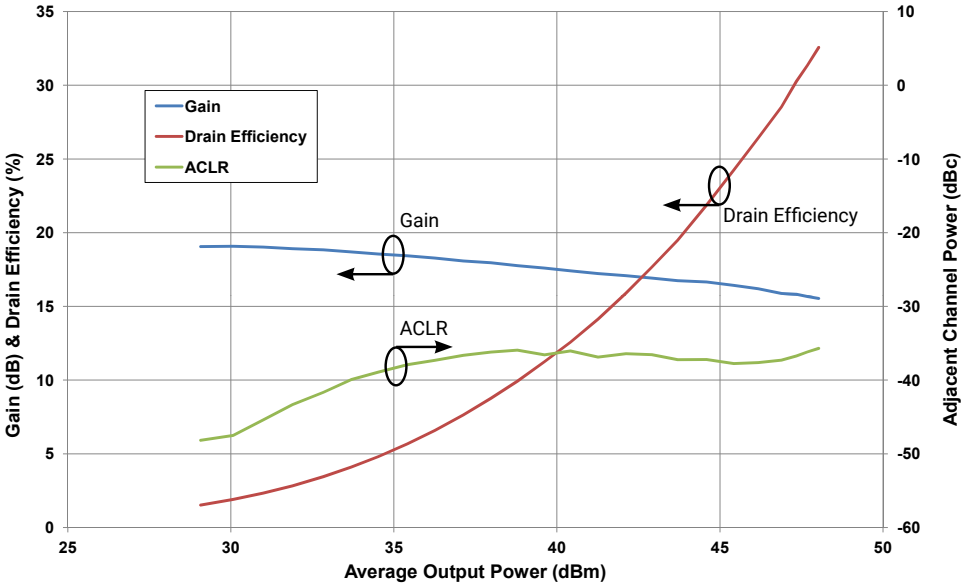
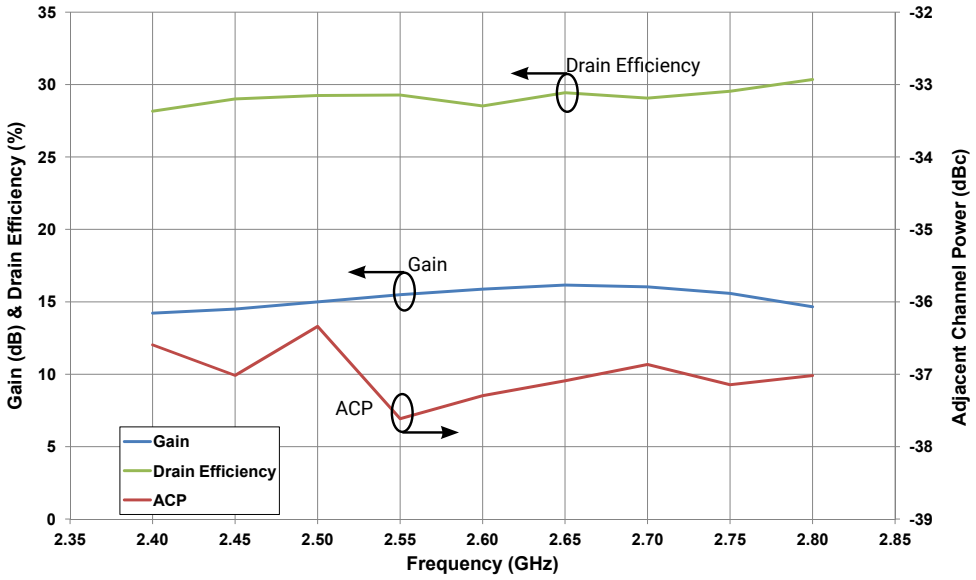


Figure 4. - Typical Linearity at P_{AVE} = 46 dBm over Frequency of the CGHV27200 measured in CGHV27200-AMP Amplifier Circuit. V_{DD} = 50 V, I_{DQ} = 1.0 A, 1c WCDMA 7.5 dB PAR



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Typical Performance

Figure 5. - Typical Linearity under DPD vs Output Power
V_{DD} = 50 V, I_{DQ} = 1.0 A, Freq = 2.6 GHz, 1c WCDMA 7.5 dB PAR

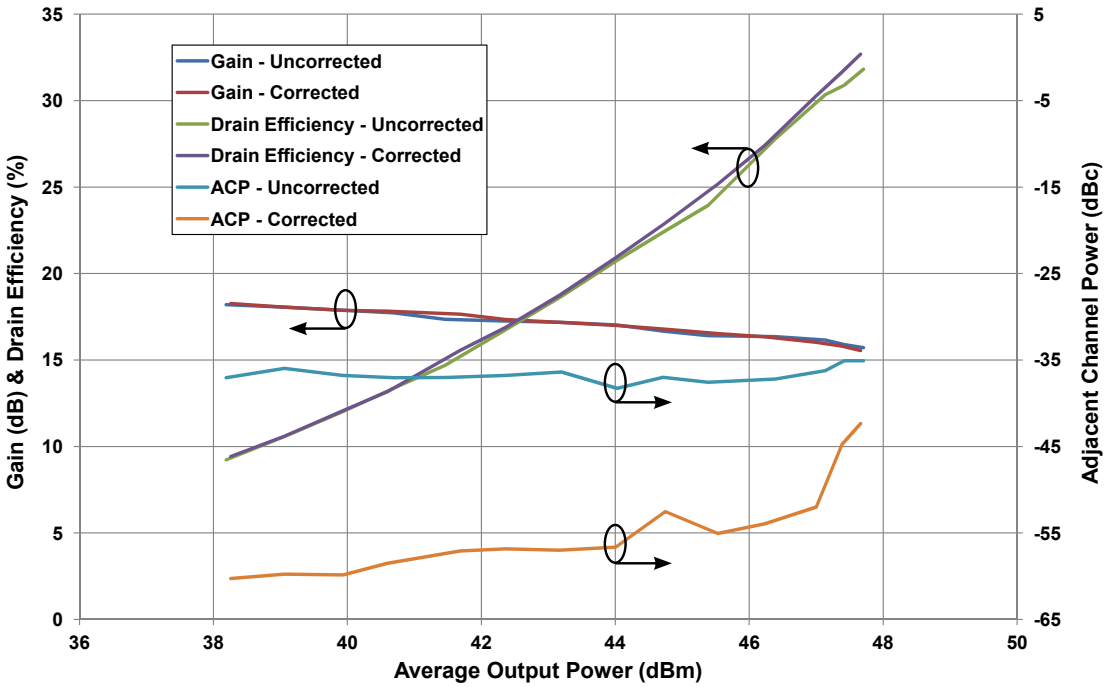
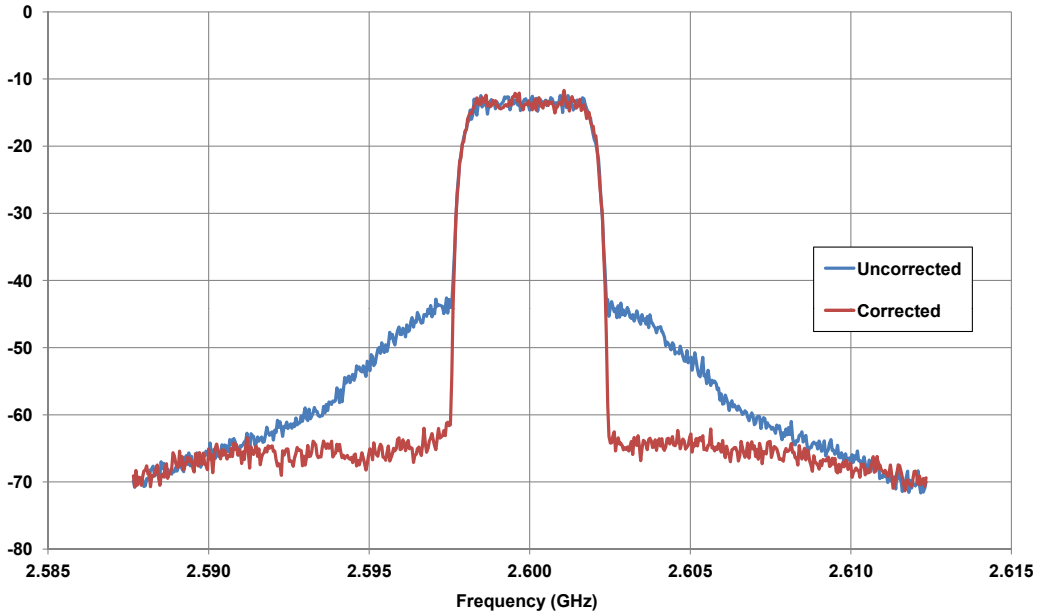


Figure 6. - Spectral Mask at P_{AVE} = 46 dBm with and without DPD
V_{DD} = 50 V, I_{DQ} = 1.0 A, 1c WCDMA 7.5 dB PAR



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Typical Performance

Figure 7. - Intermodulation Distortion Products vs Output Power
V_{DD} = 50 V, I_{DQ} = 1.0 A, Tone Spacing = 100 kHz

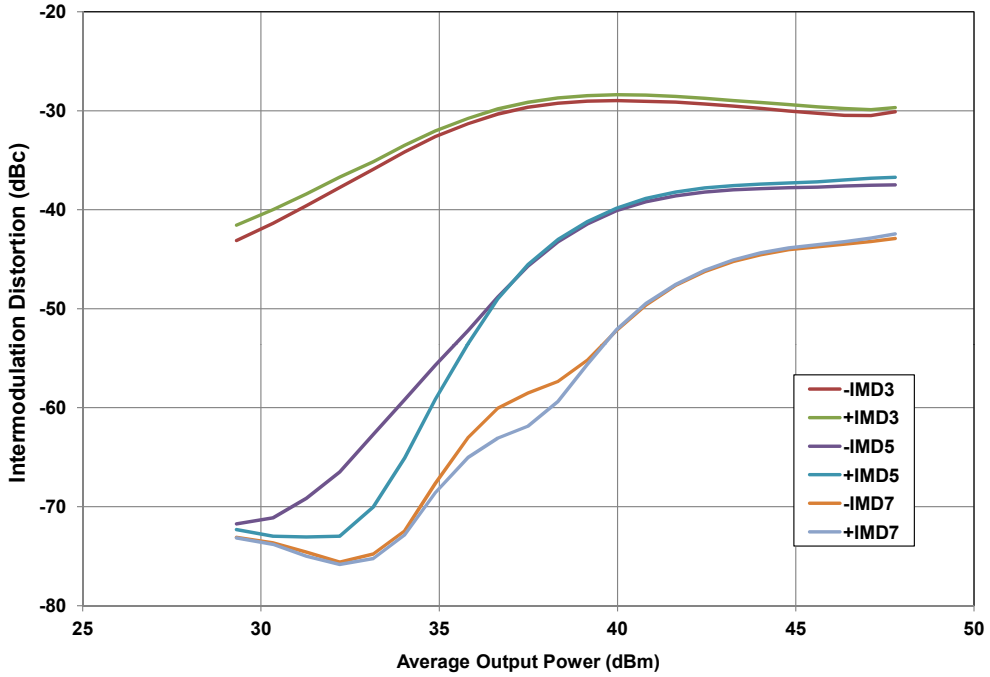
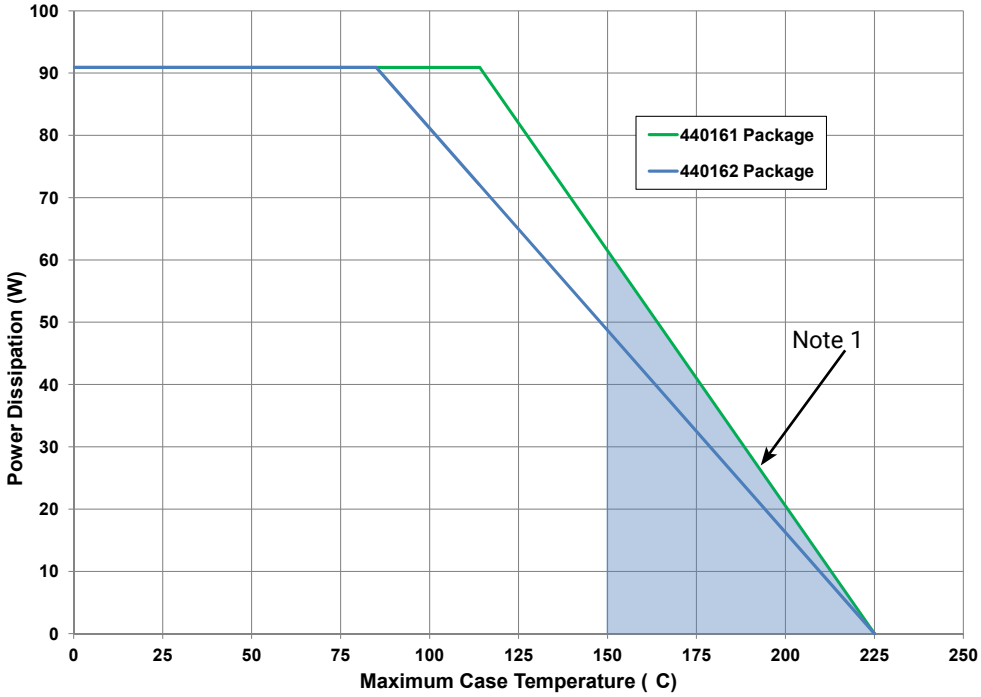


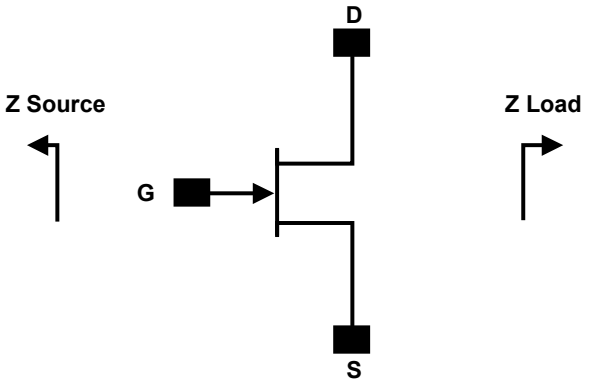
Figure 8. - Power Dissipation Derating Curve



Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Source and Load Impedances

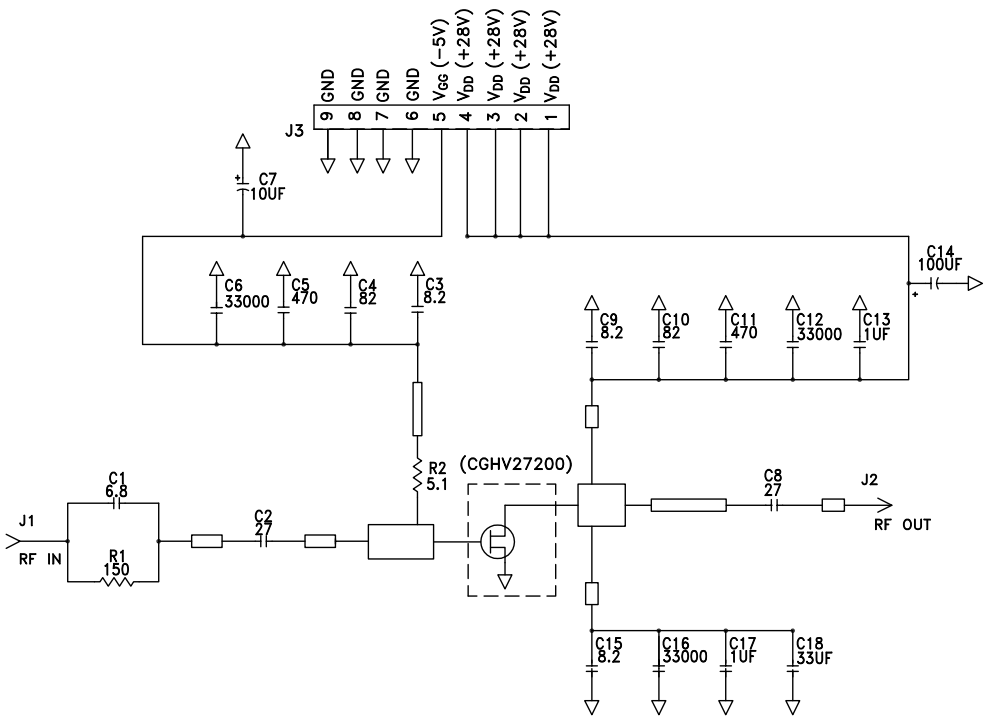


Frequency (MHz)	Z Source	Z Load
2500	11.14 - j14.20	4.66 - j0.69
2550	9.58 - j14.73	4.51 - j0.92
2600	7.99 - j14.81	4.30 - j1.12
2650	6.53 - j14.52	4.02 - j1.27
2700	5.28 - j13.97	3.70 - j1.36

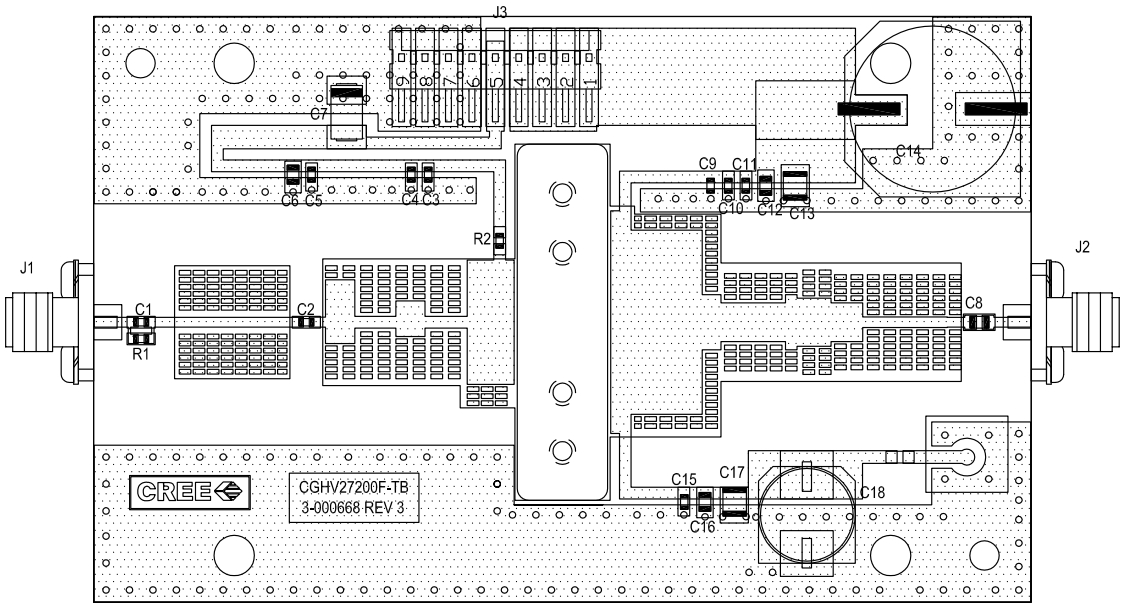
Note[1]: V_{DD} = 50 V, I_{DQ} = 1.0 A. In the 440162 package.
Note[2]: Impedances are extracted from CGHV27200-AMP demonstration circuit and are not source and load pull data derived from transistor.

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

CGHV27200-AMP Demonstration Amplifier Circuit Schematic



CGHV27200-AMP Demonstration Amplifier Circuit Outline

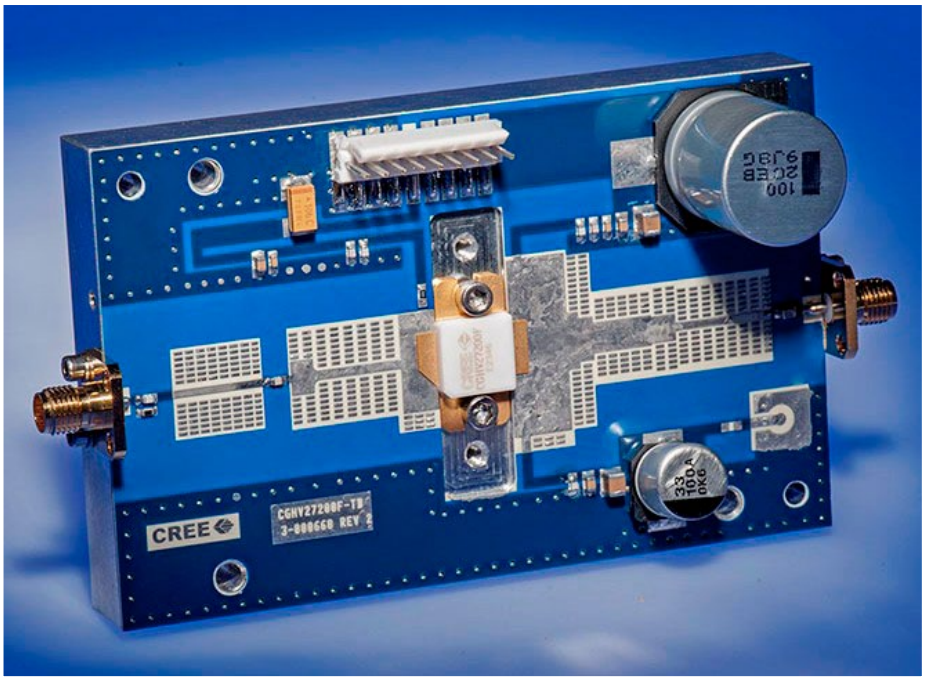


Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

CGHV27200-AMP Demonstration Amplifier Circuit Bill of Materials

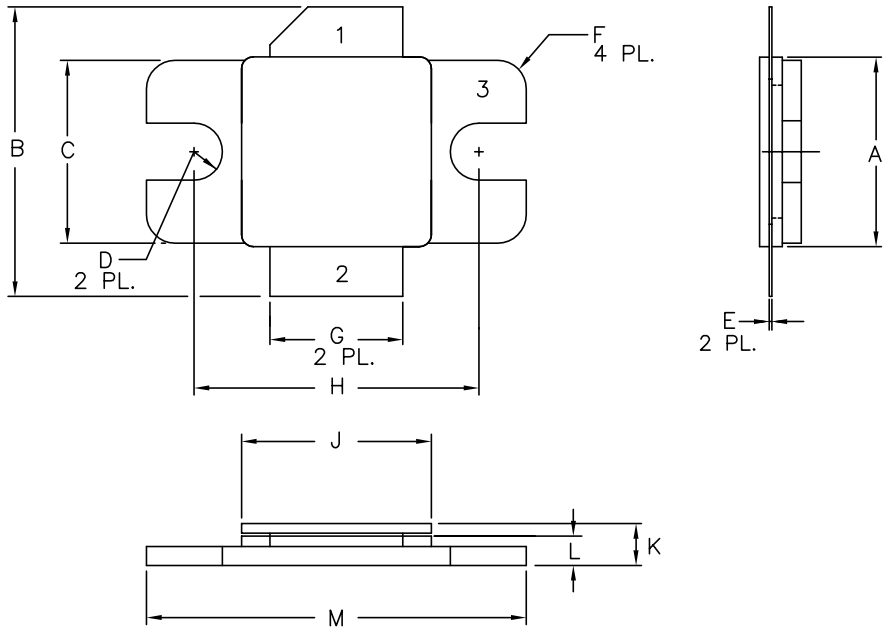
Designator	Description	Qty
R1	RES, 1/16 W, 0603, 1%, 150 OHMS	1
R2	RES, 1/16 W, 0603, 1%, 5.1 OHMS	1
C1	CAP, 6.2 pF, +/-0.25 pF, 0603, ATC600S	1
C2	CAP, 27 pF, +/-5%, 0603, ATC600S	1
C3,C9,C15	CAP, 8.2 pF, +/-0.25 pF, 0603, ATC600S	3
C4,C10	CAP, 82.0 pF, +/-5%, 0603, ATC600S	2
C5,C11	CAP, 470 pF, 5%, 100 V, 0603, X7R	2
C6,C12,C16	CAP, 33000 pF, 0805, 100 V, X7R	3
C7	CAP, 10 UF, 16V, TANTALUM	1
C8	CAP, 27 pF, +/-5%, 250 V, 0603, ATC600S	1
C13,C17	CAP, 1.0 UF, 100 V, 10%, X7R, 1210	2
C14	CAP, 100 UF, +/-20%, 160V, ELECTROLYTIC	2
C18	CAP, 33 UF, 20%, G CASE	1
J1,J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
J3	CONN, Header, RT> PLZ, 0.1 CEN, LK, 9 POS	1
	PCB, RO4350, 0.020" THK, CGHV27200	1
	2-56 SOC HD SCREW 1/4 SS	4
	#2 SPLIT LOCKWASHER SS	4
	CGHV27200	1

CGHV27200-AMP Demonstration Amplifier Circuit



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Product Dimensions CGHV27200F (Package Type — 440162)



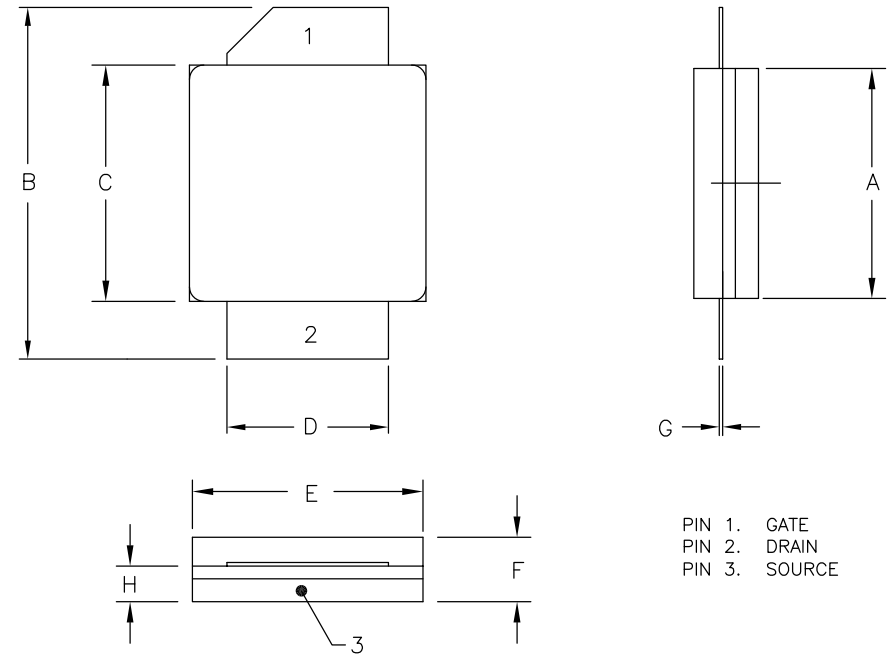
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.395	.405	10.03	10.29
B	.580	.620	14.73	15.75
C	.380	.390	9.65	9.91
D	.055	.065	1.40	1.65
E	.004	.006	0.10	0.15
F	.055	.065	1.40	1.65
G	.275	.285	6.99	7.24
H	.595	.605	15.11	15.37
J	.395	.405	10.03	10.29
K	.129	.149	3.28	3.78
L	.053	.067	1.35	1.70
M	.795	.805	20.19	20.45

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Dimensions CGHV27200P (Package Type — 440161)



NOTES:

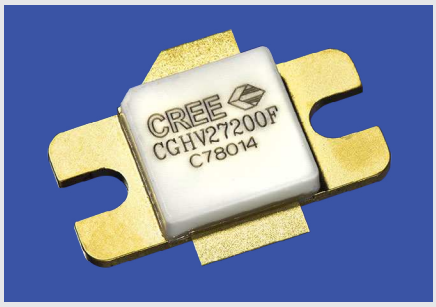
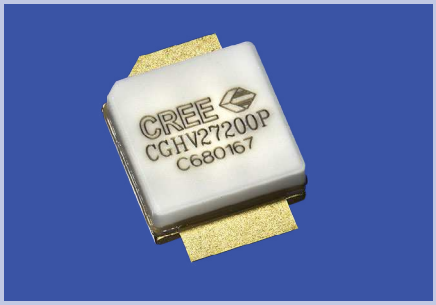
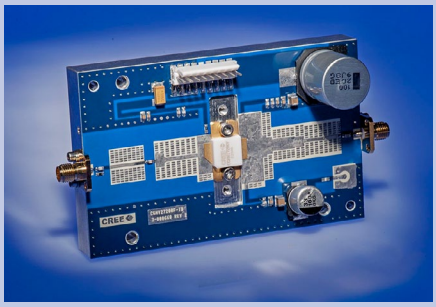
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.395	.407	10.03	10.34
B	.594	.634	15.09	16.10
C	.395	.407	10.03	10.34
D	.275	.285	6.99	7.24
E	.395	.407	10.03	10.34
F	.129	.149	3.28	3.78
G	.004	.006	0.10	0.15
H	.057	.067	1.45	1.70

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV27200F	GaN HEMT	Each	
CGHV27200P	GaN HEMT	Each	
CGHV27200-TB	Test board without GaN HEMT	Each	
CGHV27200-AMP	Test board with GaN HEMT installed	Each	

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Disclaimer

Specifications are subject to change without notice. Cree, Inc. believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Cree for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Cree. Cree makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. “Typical” parameters are the average values expected by Cree in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer’s technical experts for each application. Cree products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Cree product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility.

For more information, please contact:

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
www.cree.com/rf

Sarah Miller
Marketing
Cree, RF Components
1.919.407.5302

Ryan Baker
Marketing & Sales
Cree, RF Components
1.919.407.7816

Tom Dekker
Sales Director
Cree, RF Components
1.919.407.5639

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf